

SEMICONDUCTOR

BC212B

PNP General Purpose Amplifier

- This device is designed for general purpose amplifier application at collector currents to 100mA.
- Sourced from process 68.



1. Collector 2. Base 3. Emitter

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Absolute Maximum Ratings* T_C=25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V _{CEO}	Collector-Emitter Voltage	50	V	
V _{CBO}	Collector-Base Voltage	60	V	
V _{EBO}	Emitter-Base Voltage	5	V	
I _C	Collector Current - Continuous	100	mA	
T _{J,} T _{STG}	Operating and Storage Junction Temperature Range	- 55 ~ 150	°C	

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

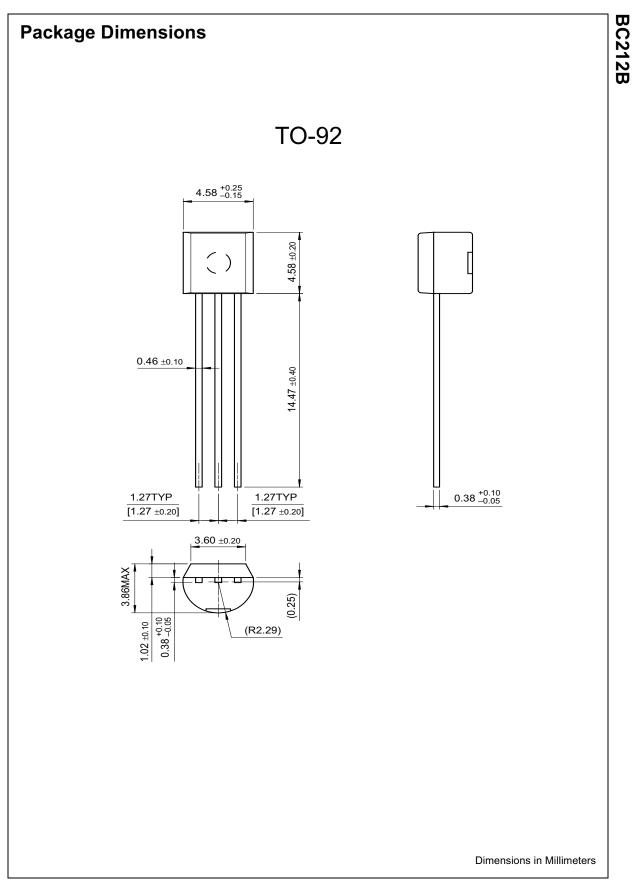
These ratings are based on a maximum junction temperature of 150°C.
 These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
Off Chara	Off Characteristics					
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 2mA	50			V
BV _{CBO}	Collector-Base Breakdown Voltage	I _C = 10μA	60			V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E = 10μA	5			V
I _{CBO}	Collector Cut-off Current	V _{CB} = 30V			15	nA
I _{EBO}	Emitter Cut-off Current	V _{EB} = 4V			15	nA
On Chara	On Characteristics*					
h _{FE}	DC Current Gain	$V_{CE} = 5V, I_{C} = 10\mu A$ $V_{CE} = 5V, I_{C} = 2mA$	40 60			
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C = 100mA, I _B = 5mA			0.6	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	I _C = 100mA, I _B = 5mA			1.4	V
V _{BE} (on)	Base-Emitter On Voltage	V _{CE} = 5V, I _C = 2mA	0.6		0.72	V
Small Signal Characteristics						
C _{ob}	Output Capacitance	V _{CE} = 10V, f = 1MHz			6	pF
h _{fe}	Small Signal Current Gain	V _{CE} = 5V, I _C = 2mA, f = 1KHz	200		400	
NF	Noise Figure	V_{CE} = 5V, I _C = 200µA, f = 1KHz R _G = 2KΩ, BW = 200Hz			10	dB

* Pulse Test: Pulse Width < 300µs, Duty Cycle < 2.0%

ol	Characteristics T _A =25°C unless otherwise noted Parameter	Max.	Units
	Total Device Dissipation	350	mW
	Derate above 25°C	2.8	mW/°C
	Thermal Resistance, Junction to Ambient	357	°C/W
	Thermal Resistance, Junction to Case	125	°C/W



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